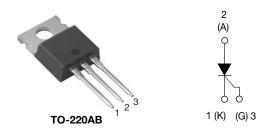


VS-40TTS12PbF, VS-40TTS12-M3

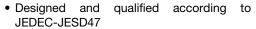
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Thyristor High Voltage, Phase Control SCR, 40 A

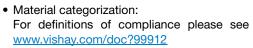


PRODUCT SUMMARY					
Package	TO-220AB				
Diode variation	Single SCR				
I _{T(AV)}	25 A				
V_{DRM}/V_{RRM}	1200 V				
V_{TM}	1.6 V				
I _{GT}	35 mA				
TJ	- 40 °C to 140 °C				

FEATURES













APPLICATIONS

 Typical usage is in input rectification crowbar (soft start) and AC switch in motor control, UPS, welding, and battery charge

DESCRIPTION

The VS-40TTS12... high voltage series of silicon controlled rectifiers are specifically designed for medium power switching and phase control applications. The glass passivation technology used has reliable operation up to 140 °C junction temperature.

MAJOR RATINGS AND CHARACTERISTICS						
PARAMETER	TEST CONDITIONS	VALUES	UNITS			
I _{T(AV)}	Sinusoidal waveform	25	A			
I _{RMS}		40	^			
V _{RRM} /V _{DRM}		1200	V			
I _{TSM}		350	A			
V _T	T _J = 25 °C	1.6	V			
dV/dt		500	V/µs			
dl/dt		150	A/μs			
TJ		- 40 to 140	°C			

VOLTAGE RATINGS							
PART NUMBER	V _{RRM} , MAXIMUM PEAK REVERSE VOLTAGE V	V _{DRM} , MAXIMUM PEAK DIRECT VOLTAGE V	°C T _J				
VS-40TTS12PbF, VS-40TTS12-M3	1200	1200	- 25 to 140				

VS-40TTS12PbF, VS-40TTS12-M3

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ABSOLUTE MAXIMUM RATINGS	5			
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum average on-state current	I _{T(AV)}	T _C = 93 °C, 180° conduction half sine wave	25	
Maximum RMS on-state current	I _{RMS}		40	Α
Maximum peak, one-cycle		10 ms sine pulse, rated V _{RRM} applied	300	
non-repetitive surge current	I _{TSM}	10 ms sine pulse, no voltage reapplied	350	
Maximum I ² t for fusing	l ² t	10 ms sine pulse, rated V _{RRM} applied	450	A ² s
Maximum i-t for fusing	1-1	10 ms sine pulse, no voltage reapplied	630	A ² S
Maximum I ² √t for fusing	l²√t	t = 0.1 to 10 ms, no voltage reapplied	6300	A ² √s
Maximum on-state voltage	V_{TM}	80 A, T _J = 25 °C	1.6	V
Low level value of on-state slope resistance	r _t	T ₁ = 140 °C	11.4	mΩ
Low level value of threshold voltage	V _{T(TO)}	1J = 140 C	0.96	V
Maximum reverse and direct leakage	1 /1	$T_J = 25 ^{\circ}C$	0.5	
current	I_{RRM}/I_{DRM}	$V_R = Rated V_{RRM}/V_{DRM}$	12	
Holding current	I _H	Anode supply = 6 V, resistive load, initial I_T = 1 A, T_J = 25 °C	100	mA
Maximum latching current	ΙL	Anode supply = 6 V, resistive load, T _J = 25 °C	200	
Maximum rate of rise of off-state voltage	dV/dt	$T_J = T_J \text{ max., linear to } 80 ^{\circ}\text{C}, V_{DRM} = R_g - k = \text{Open}$	500	V/µs
Maximum rate of rise of turned-on current	dl/dt		150	A/μs

TRIGGERING						
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS		
Maximum peak gate power	P_{GM}		8.0	W		
Maximum average gate power	P _{G(AV)}		2.0	VV		
Maximum peak positive gate current	+ I _{GM}		1.5	Α		
Maximum peak negative gate voltage	- V _{GM}		10	V		
Maximum required DC gate current to trigger	I _{GT}	Anode supply = 6 V, resistive load, T _J = 25 °C	35	mA		
Maximum required DC gate voltage to trigger	V _{GT}	Anode supply = 6 V, resistive load, T _J = 25 °C	1.3	V		
Maximum DC gate voltage not to trigger	V_{GD}	T 140 °C V Poted value	0.2			
Maximum DC gate current not to trigger	I_{GD}	T _J = 140 °C, V _{DRM} = Rated value	1.5	mA		

SWITCHING						
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS		
Typical turn-on time	t _{gt}	T _J = 25 °C	0.9			
Typical reverse recovery time	t _{rr}	T _{.1} = 140 °C	4	μs		
Typical turn-off time	t _q	1j = 140 C	110			

THERMAL AND MECHANICAL SPECIFICATIONS						
PARAMETER		SYMBOL TEST CONDITIONS		VALUES	UNITS	
Maximum junction and storage temperature range		T _J , T _{Stg}		- 40 to 140	°C	
Maximum thermal resistance, junction to case		R_{thJC}	DC operation	0.8		
Maximum thermal resistance, junction to ambient		R _{thJA}		60	°C/W	
Typical thermal resistance, case to heatsink		R _{thCS}	Mounting surface, smooth and greased	0.5		
Approximate weight				2	g	
Approximate weight				0.07	OZ.	
Mounting torque	minimum			6 (5)	kgf · cm	
Mounting torque	maximum			12 (10)	($lbf \cdot in$)	
Marking device Case style TO-220AB 40TT		S12				

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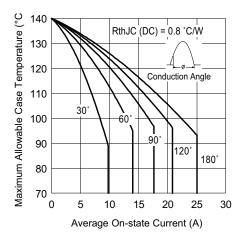


Fig. 1 - Current Rating Characteristics

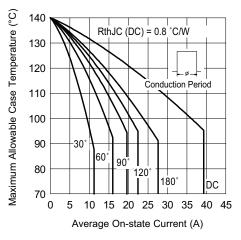


Fig. 2 - Current Rating Characteristics

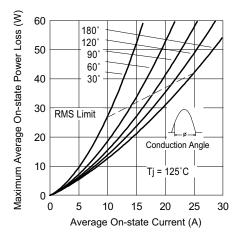


Fig. 3 - On-State Power Loss Characteristics

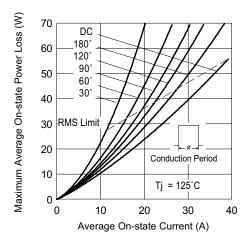


Fig. 4 - On-State Power Loss Characteristics

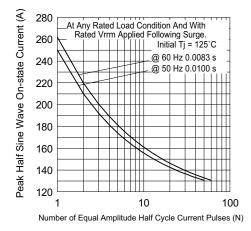


Fig. 5 - Maximum Non-Repetitive Surge Current

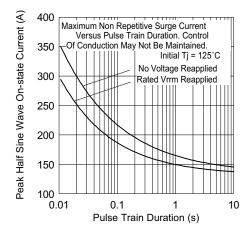


Fig. 6 - Maximum Non-Repetitive Surge Current

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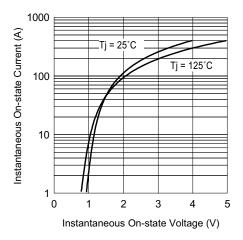


Fig. 7 - On-State Voltage Drop Characteristics

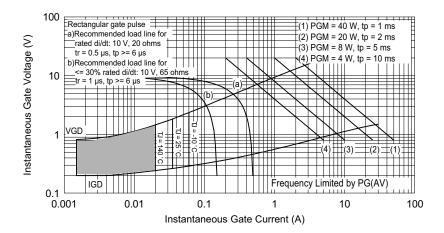


Fig. 8 - Gate Characteristics

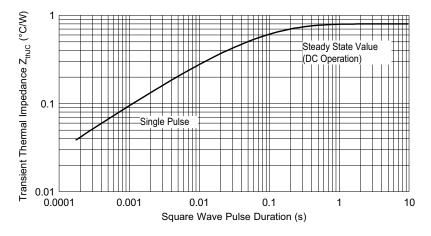


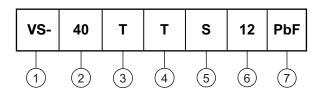
Fig. 9 - Thermal Impedance Z_{thJC} Characteristics

VS-40TTS12PbF, VS-40TTS12-M3

Vishay Semiconductors

ORDERING INFORMATION TABLE

Device code



1 - Vishay Semiconductors product

2 - Current rating, RMS value

3 - Circuit configuration:

T = Single thyristor

4 - Package:

T = TO-220

5 - Type of silicon:

S = Standard recovery rectifier

6 - Voltage rating (12 = 1200 V)

7 - Environmental digit:

PbF = Lead (Pb)-free and RoHS compliant

-M3 = Halogen-free, RoHS compliant, and terminations lead (Pb)-free

ORDERING INFORMATION (Example)						
PREFERRED P/N QUANTITY PER T/R MINIMUM ORDER QUANTITY PACKAGING DESCRIPTION						
VS-40TTS12PbF	50	1000	Antistatic plastic tubes			
VS-40TTS12-M3	50	1000	Antistatic plastic tubes			

LINKS TO RELATED DOCUMENTS						
Dimensions <u>www.vishay.com/doc?95222</u>						
Dort marking information	TO-220AB PbF	www.vishay.com/doc?95225				
Part marking information	TO-220AB -M3	www.vishay.com/doc?95028				



Vishay Semiconductors

TO-220AB

DIMENSIONS in millimeters and inches



Lead assignments

Diodes

- 1. Anode/open
- 2. Cathode
- 3. Anode

Conforms to JEDEC outline TO-220AB

SYMBOL	MILLIN	IETERS	INC	NOTES	
STMBOL	MIN.	MAX.	MIN.	MAX.	NOTES
Α	4.25	4.65	0.167	0.183	
A1	1.14	1.40	0.045	0.055	
A2	2.56	2.92	0.101	0.115	
b	0.69	1.01	0.027	0.040	
b1	0.38	0.97	0.015	0.038	4
b2	1.20	1.73	0.047	0.068	
b3	1.14	1.73	0.045	0.068	4
С	0.36	0.61	0.014	0.024	
c1	0.36	0.56	0.014	0.022	4
D	14.85	15.25	0.585	0.600	3
D1	8.38	9.02	0.330	0.355	
D2	11.68	12.88	0.460	0.507	6

SYMBOL	MILLIM	IETERS	INC	HES	NOTES
STIMBOL	MIN.	MAX.	MIN.	MAX.	NOTES
E	10.11	10.51	0.398	0.414	3, 6
E1	6.86	8.89	0.270	0.350	6
E2	-	0.76	-	0.030	7
е	2.41	2.67	0.095	0.105	
e1	4.88	5.28	0.192	0.208	
H1	6.09	6.48	0.240	0.255	6, 7
L	13.52	14.02	0.532	0.552	
L1	3.32	3.82	0.131	0.150	2
ØΡ	3.54	3.73	0.139	0.147	
Q	2.60	3.00	0.102	0.118	
θ	90° t	o 93°	90° t	o 93°	
		•	•	•	

Notes

- (1) Dimensioning and tolerancing as per ASME Y14.5M-1994
- (2) Lead dimension and finish uncontrolled in L1
- (3) Dimension D, D1 and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body
- (4) Dimension b1, b3 and c1 apply to base metal only
- (5) Controlling dimensions: inches
- (6) Thermal pad contour optional within dimensions E, H1, D2 and E1
- (7) Dimensions E2 x H1 define a zone where stamping and singulation irregularities are allowed
- (8) Outline conforms to JEDEC TO-220, except A2 (maximum) and D2 (minimum) where dimensions are derived from the actual package outline

Lead tip



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